

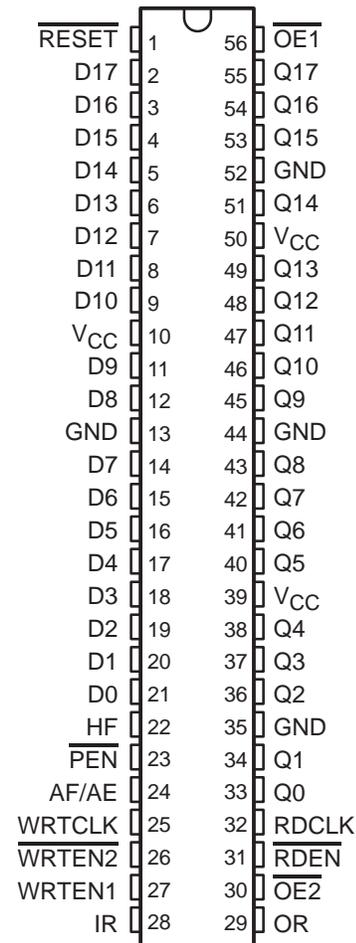
SN74ACT7813

64 × 18 CLOCKED FIRST-IN, FIRST-OUT MEMORY

SCAS199B – JANUARY 1991 – REVISED APRIL 1998

- Member of the Texas Instruments Widebus™ Family
- Free-Running Read and Write Clocks Can Be Asynchronous or Coincident
- Read and Write Operations Synchronized to Independent System Clocks
- Input-Ready Flag Synchronized to Write Clock
- Output-Ready Flag Synchronized to Read Clock
- 64 Words by 18 Bits
- Low-Power Advanced CMOS Technology
- Half-Full Flag and Programmable Almost-Full/Almost-Empty Flag
- Bidirectional Configuration and Width Expansion Without Additional Logic
- Fast Access Times of 12 ns With a 50-pF Load and All Data Outputs Switching Simultaneously
- Data Rates up to 67 MHz
- Pin-to-Pin Compatible With SN74ACT7803 and SN74ACT7805
- Packaged in Shrink Small-Outline 300-mil Package Using 25-mil Center-to-Center Spacing

**DL PACKAGE
(TOP VIEW)**



description

The SN74ACT7813 is a 64-word × 18-bit FIFO suited for buffering asynchronous datapaths up to 67-MHz clock rates and 12-ns access times. Two devices can be configured for bidirectional data buffering without additional logic. Multiple distributed V_{CC} and GND pins, along with Texas Instruments patented output edge control (OEC™) circuit, dampen simultaneous switching noise.

The write clock (WRTCLK) and read clock (RDCLK) are free running and can be asynchronous or coincident. Data is written to memory on the rising edge of WRTCLK when WRTEN1 is high, WRTEN2 is low, and input ready (IR) is high. Data is read from memory on the rising edge of RDCLK when RDEN, OE1, and OE2 are low and output ready (OR) is high. The first word written to memory is clocked through to the output buffer regardless of the RDEN, OE1, and OE2 levels. The OR flag indicates that valid data is present on the output buffer.

The FIFO can be reset asynchronously to WRTCLK and RDCLK. RESET must be asserted while at least four WRTCLK and four RDCLK rising edges occur to clear the synchronizing registers. Resetting the FIFO initializes the IR, OR, and half-full (HF) flags low and the almost-full/almost-empty (AF/AE) flag high. The FIFO must be reset upon power up.

The SN74ACT7813 is characterized for operation from 0°C to 70°C.



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PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.



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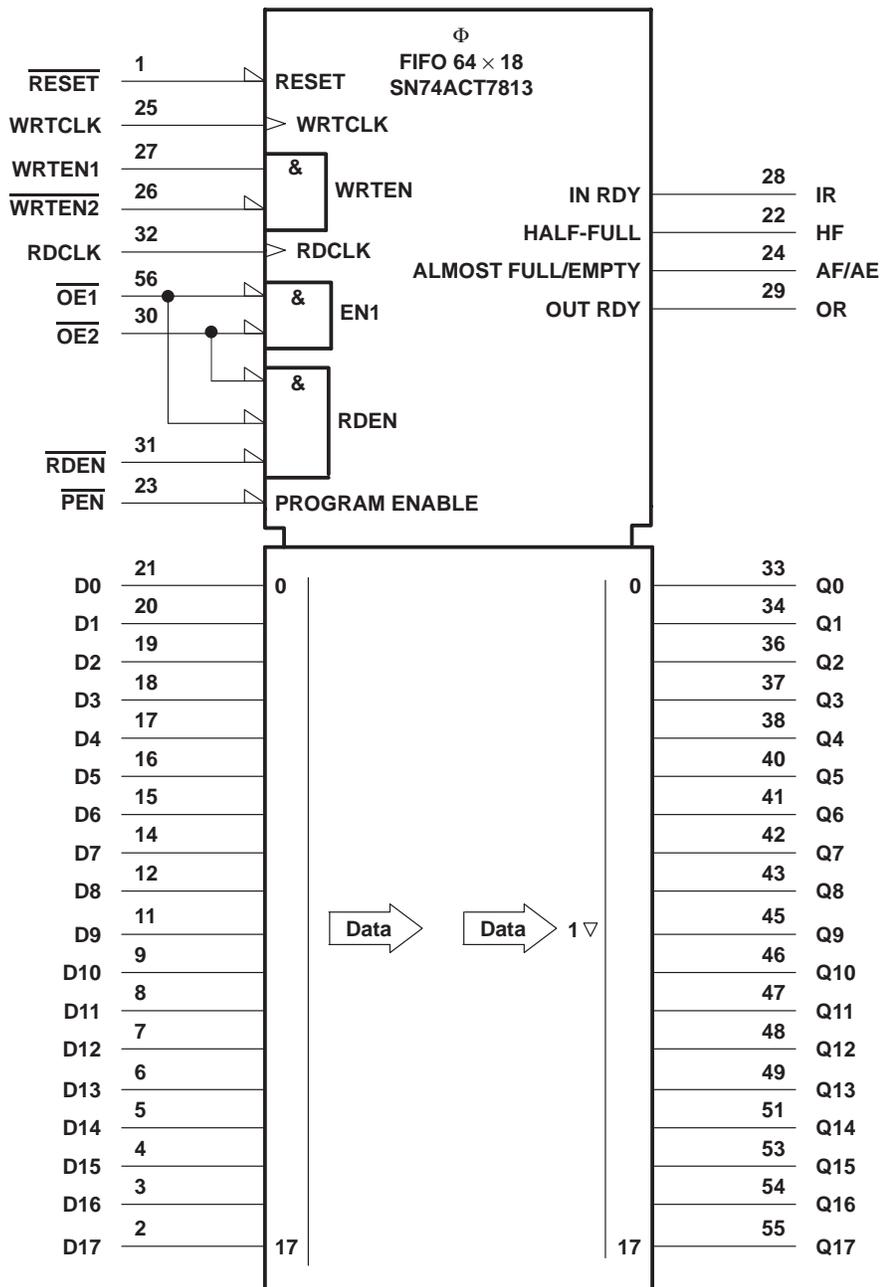
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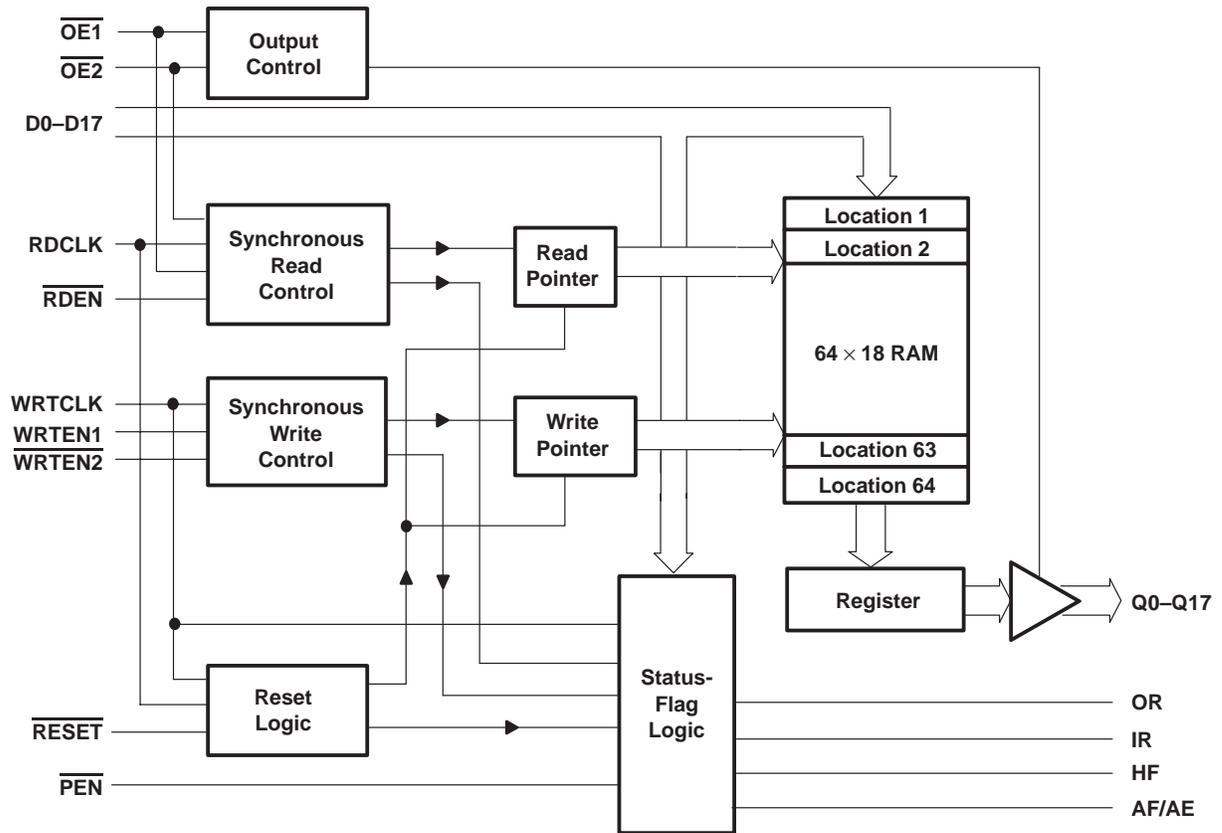
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logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

functional block diagram



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Terminal Functions

TERMINAL NAME	NO.	I/O	DESCRIPTION
AF/AE	24	O	Almost-full/almost-empty flag. Depth offset values can be programmed for AF/AE, or the default value of 8 can be used for both the AE offset (X) and the AF offset (Y). AF/AE is high when memory contains X or fewer words or (64 – Y) or more words. AF/AE is high after reset.
D0–D17	21–14, 12–11, 9–2	I	18-bit data input port
HF	22	O	Half-full flag. HF is high when the FIFO memory contains 32 or more words. HF is low after reset.
IR	28	O	Input-ready flag. IR is synchronized to the low-to-high transition of WRTCLK. When IR is low, the FIFO is full and writes are disabled. IR is low during reset and goes high on the second low-to-high transition of WRTCLK after reset.
$\overline{OE1}$, $\overline{OE2}$	56, 30	I	Output enables. When $\overline{OE1}$, $\overline{OE2}$, and \overline{RDEN} are low and OR is high, data is read from the FIFO on a low-to-high transition of RDCLK. When either $\overline{OE1}$ or $\overline{OE2}$ is high, reads are disabled and the data outputs are in the high-impedance state.
OR	29	O	Output-ready flag. OR is synchronized to the low-to-high transition of RDCLK. When OR is low, the FIFO is empty and reads are disabled. Ready data is present on Q0–Q17 when OR is high. OR is low during reset and goes high on the third low-to-high transition of RDCLK after the first word is loaded to empty memory.
\overline{PEN}	23	I	Program enable. After reset and before the first word is written to the FIFO, the binary value on D0–D4 is latched as an AF/AE offset value when \overline{PEN} is low and WRTCLK is high.
Q0–Q17	33–34, 36–38, 40–43, 45–49, 51, 53–55	O	The 18-bit data output port. After the first valid write to empty memory, the first word is output on Q0–Q17 on the third rising edge of RDCLK. OR also is asserted high at this time to indicate ready data. When OR is low, the last word read from the FIFO is present on Q0–Q17.
RDCLK	32	I	Read clock. RDCLK is a continuous clock and can be asynchronous or coincident to WRTCLK. A low-to-high transition of RDCLK reads data from memory when $\overline{OE1}$, $\overline{OE2}$, and \overline{RDEN} are low and OR is high. OR is synchronous to the low-to-high transition of RDCLK.
\overline{RDEN}	31	I	Read enable. When \overline{RDEN} , $\overline{OE1}$, and $\overline{OE2}$ are low and OR is high, data is read from the FIFO on the low-to-high transition of RDCLK.
\overline{RESET}	1	I	Reset. To reset the FIFO, four low-to-high transitions of RDCLK and four low-to-high transitions of WRTCLK must occur while \overline{RESET} is low. This sets HF, IR, and OR low and AF/AE high.
WRTCLK	25	I	Write clock. WRTCLK is a continuous clock and can be asynchronous or coincident to RDCLK. A low-to-high transition of WRTCLK writes data to memory when WRTEN2 is low, WRTEN1 is high, and IR is high. IR is synchronous to the low-to-high transition of WRTCLK.
$\overline{WRTEN1}$, $\overline{WRTEN2}$	27, 26	I	Write enables. When WRTEN1 is high, $\overline{WRTEN2}$ is low, and IR is high, data is written to the FIFO on a low-to-high transition of WRTCLK.



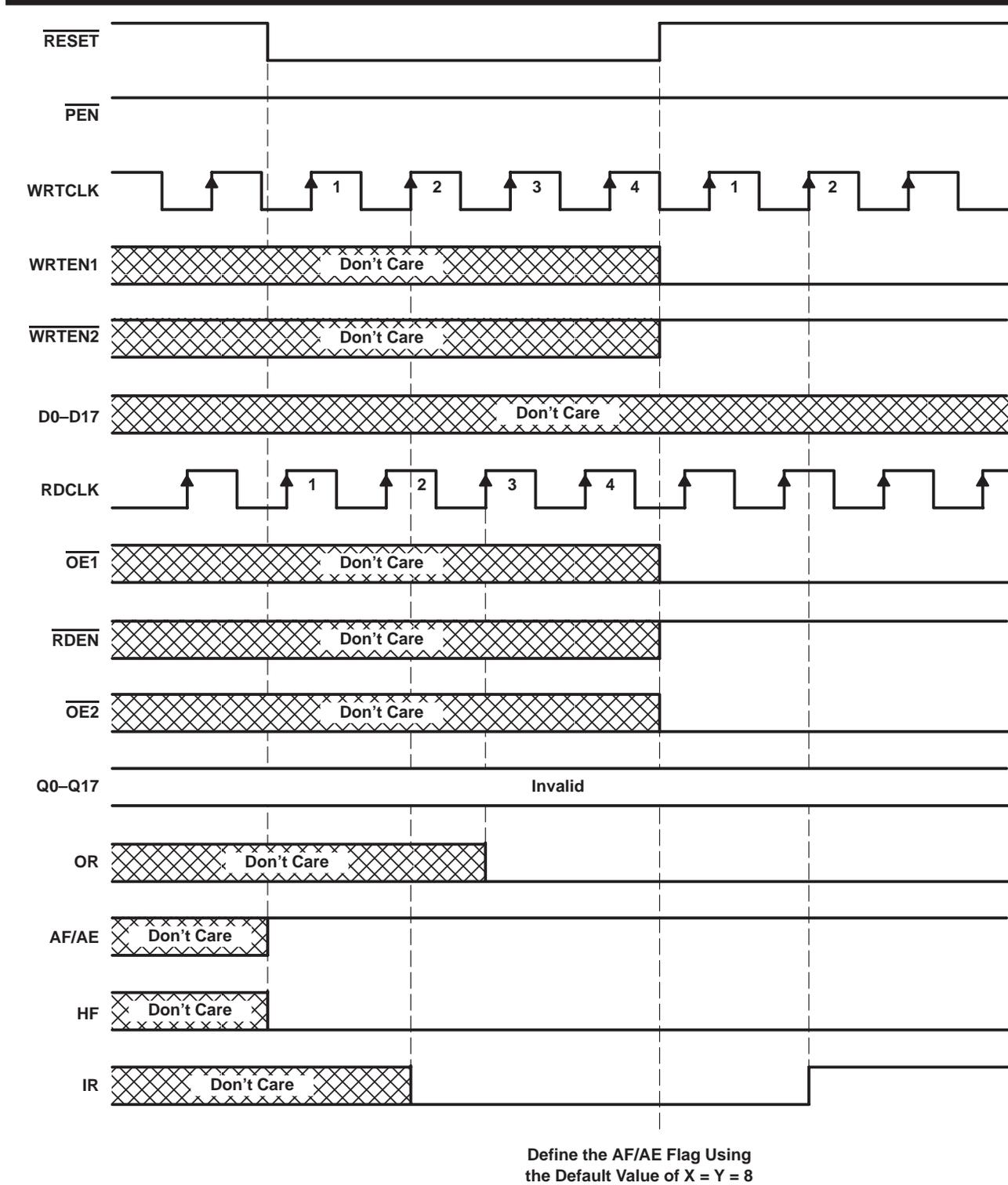


Figure 1. Reset Cycle

SN74ACT7813 64 × 18 CLOCKED FIRST-IN, FIRST-OUT MEMORY

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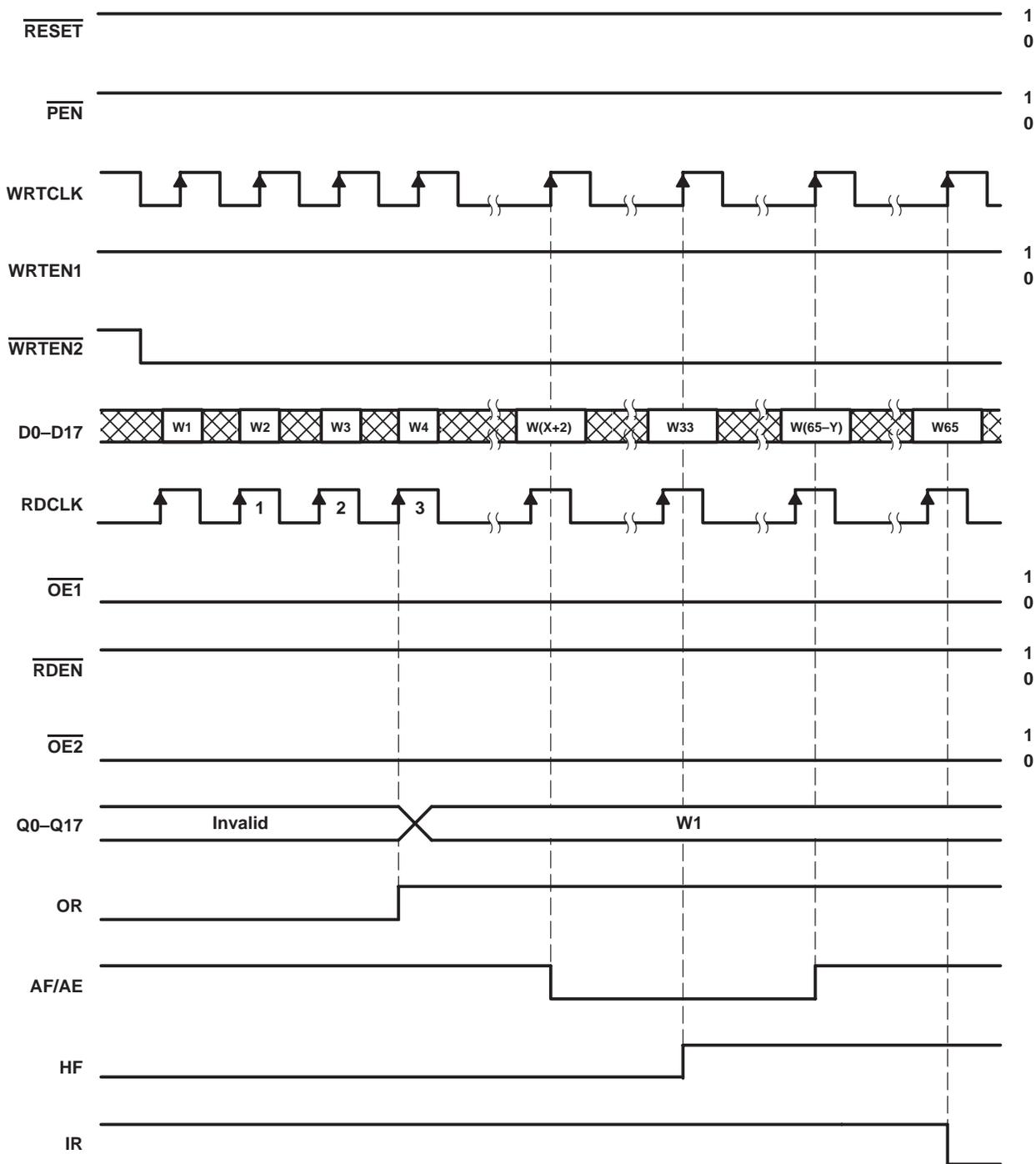


Figure 2. Write Cycle



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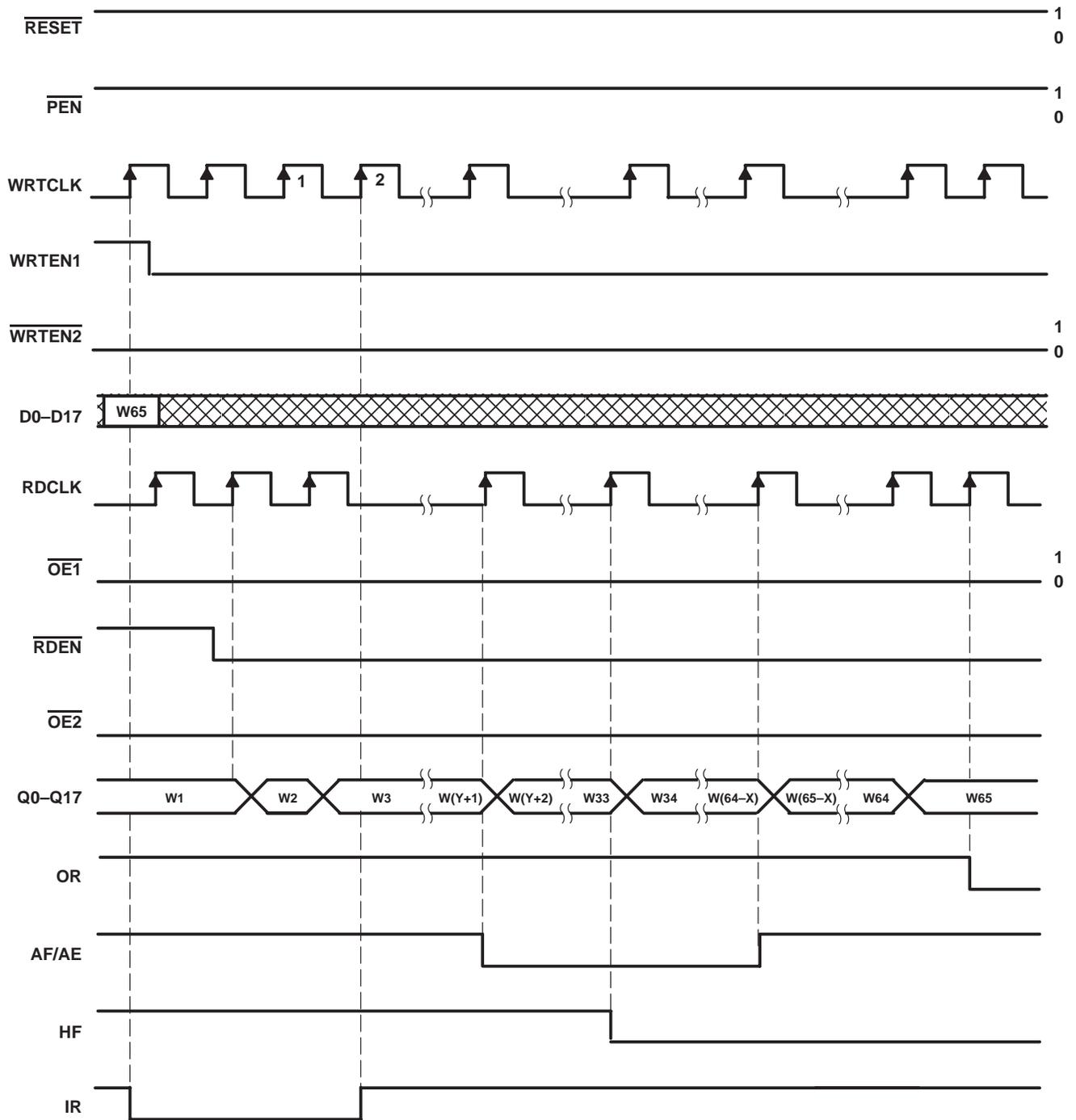


Figure 3. Read Cycle

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offset values for AF/AE

The AF/AE flag has two programmable limits: the AE offset value (X) and the AF offset value (Y). They can be programmed after the FIFO is reset and before the first word is written to memory. If the offsets are not programmed, the default values of $X = Y = 8$ are used. The AF/AE flag is high when the FIFO contains X or fewer words or $(64 - Y)$ or more words.

Program enable (\overline{PEN}) should be held high throughout the reset cycle. \overline{PEN} can be brought low only when IR is high and WRTCLK is low. On the following low-to-high transition of WRTCLK, the binary value on D0–D4 is stored as the AE offset value (X) and the AF offset value (Y). Holding \overline{PEN} low for another low-to-high transition of WRTCLK reprograms Y to the binary value on D0–D4 at the time of the second WRTCLK low-to-high transition. When the offsets are being programmed, writes to the FIFO memory are disabled regardless of the state of the write enables (WRTEN1, WRTEN2). A maximum value of 31 can be programmed for either X or Y (see Figure 4). To use the default values of $X = Y = 8$, \overline{PEN} must be held high.

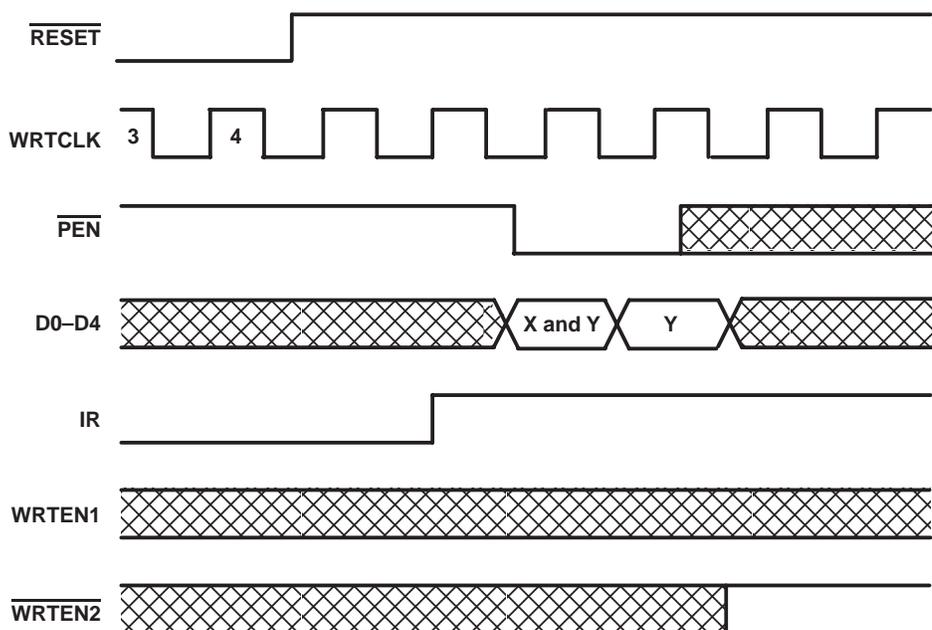


Figure 4. Programming X and Y Separately

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC}	-0.5 V to 7 V
Input voltage range, V_I	-0.5 V to 7 V
Voltage range applied to a disabled 3-state output	-0.5 V to 5.5 V
Package thermal impedance, θ_{JA} (see Note 1)	74°C/W
Storage temperature range, T_{stg}	-65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: The package thermal impedance is calculated in accordance with JESD 51.

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recommended operating conditions

		'ACT7813-15		'ACT7813-20		'ACT7813-25		'ACT7813-40		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
V _{CC}	Supply voltage	4.5	5.5	4.5	5.5	4.5	5.5	4.5	5.5	V
V _{IH}	High-level input voltage	2		2		2		2		V
V _{IL}	Low-level input voltage		0.8		0.8		0.8		0.8	V
I _{OH}	High-level output current		–8		–8		–8		–8	mA
I _{OL}	Low-level output current		16		16		16		16	mA
	Flags		8		8		8		8	
T _A	Operating free-air temperature	0	70	0	70	0	70	0	70	°C

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP [†]	MAX	UNIT
V _{OH}		V _{CC} = 4.5 V,	I _{OH} = –8 mA	2.4			V
V _{OL}	Flags	V _{CC} = 4.5 V,	I _{OL} = 8 mA			0.5	V
	Q outputs	V _{CC} = 4.5 V,	I _{OL} = 16 mA			0.5	
I _I		V _{CC} = 5.5 V,	V _I = V _{CC} or 0			±5	μA
I _{OZ}		V _{CC} = 5.5 V,	V _O = V _{CC} or 0			±5	μA
I _{CC}		V _I = V _{CC} – 0.2 V or 0				400	μA
ΔI _{CC} [‡]		V _{CC} = 5.5 V,	One input at 3.4 V, Other inputs at V _{CC} or GND			1	mA
C _i		V _I = 0,	f = 1 MHz			4	pF
C _o		V _O = 0,	f = 1 MHz			8	pF

[†] All typical values are at V_{CC} = 5 V, T_A = 25°C.

[‡] This is the supply current for each input that is at one of the specified TTL voltage levels rather than 0 V or V_{CC}.

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timing requirements over recommended operating conditions (unless otherwise noted) (see Figure 5)

		'ACT7813-15		'ACT7813-20		'ACT7813-25		'ACT7813-40		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f _{clock}	Clock frequency	67		50		40		25		MHz
t _w	Pulse duration	WRTCLK high or low		6	7	8	12			ns
		RDCLK high or low		6	7	8	12			
		PEN low		8	9	9	12			
t _{su}	Setup time	D0–D17 before WRTCLK↑		4	5	5	5			ns
		WRTEN1, WRTEN2 before WRTCLK↑		4	5	5	5			
		OE1, OE2 before RDCLK↑		5	5	6	6			
		RDEN before RDCLK↑		4	5	5	5			
		Reset: RESET low before first WRTCLK↑ and RDCLK↑†		5	6	6	6			
		PEN before WRTCLK↑		5	6	6	6			
t _h	Hold time	D0–D17 after WRTCLK↑		0	0	0	0			ns
		WRTEN1, WRTEN2 after WRTCLK↑		0	0	0	0			
		OE1, OE2, RDEN after RDCLK↑		0	0	0	0			
		Reset: RESET low after fourth WRTCLK↑ and RDCLK↑†		2	2	2	2			
		PEN high after WRTCLK↓		0	0	0	0			
		PEN low after WRTCLK↑		2	2	2	2			

† To permit the clock pulse to be utilized for reset purposes

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (see Figure 5)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	'ACT7813-15			'ACT7813-20		'ACT7813-25		'ACT7813-40		UNIT
			MIN	TYP‡	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f _{max}	WRTCLK or RDCLK		67			50		40		25		MHz
t _{pd}	RDCLK↑	Any Q	4	9.5	12	4	13	4	15	4	20	ns
t _{pd} §	RDCLK↑	Any Q	8.5									ns
t _{pd}	WRTCLK↑	IR	3		8.5	3	11	3	13	3	15	ns
	RDCLK↑	OR	3		8.5	3	11	3	13	3	15	
	WRTCLK↑	AF/AE	7		16.5	7	19	7	21	7	23	
	RDCLK↑		7		17	7	19	7	21	7	23	
t _{PLH}	WRTCLK↑	HF	7		15	7	17	7	19	7	21	ns
t _{PHL}	RDCLK↑	HF	7		15.5	7	18	7	20	7	22	ns
t _{PLH}	RESET low	AF/AE	2		9	2	11	2	13	2	15	ns
t _{PHL}	RESET low	HF	2		10	2	12	2	14	2	16	ns
t _{en}	OE1, OE2	Any Q	2		8.5	2	11	2	11	2	11	ns
t _{dis}	OE1, OE2	Any Q	2		9.5	2	11	2	14	2	14	ns

‡ All typical values are at V_{CC} = 5 V, T_A = 25°C.

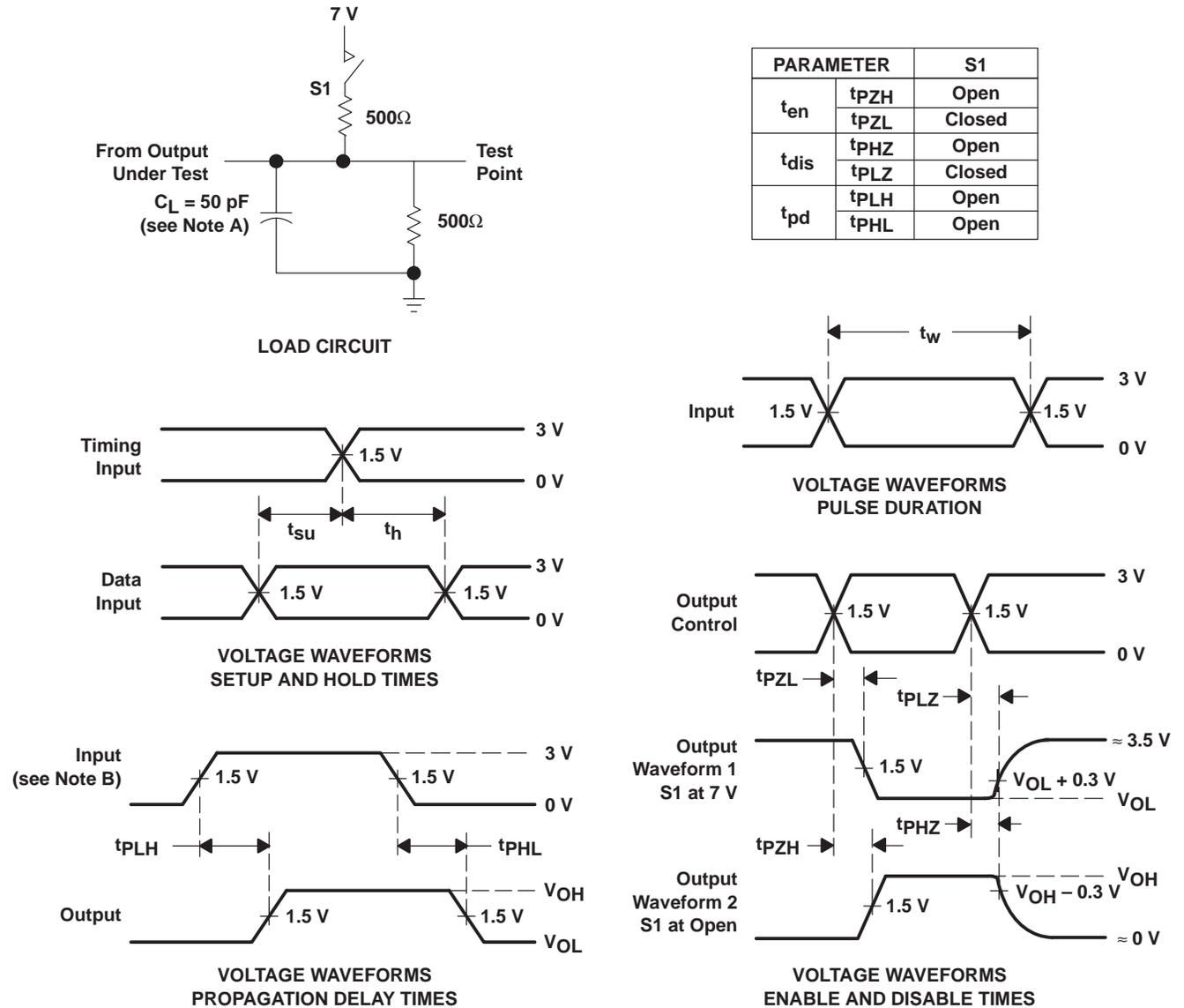
§ This parameter is measured with a 30-pF load (see Figure 6).



operating characteristics, $V_{CC} = 5\text{ V}$, $T_A = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance	Outputs enabled $C_L = 50\text{ pF}$, $f = 5\text{ MHz}$	53	pF

PARAMETER MEASUREMENT INFORMATION



NOTE A: C_L includes probe and jig capacitance.

Figure 5. Load Circuit and Voltage Waveforms

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TYPICAL CHARACTERISTICS

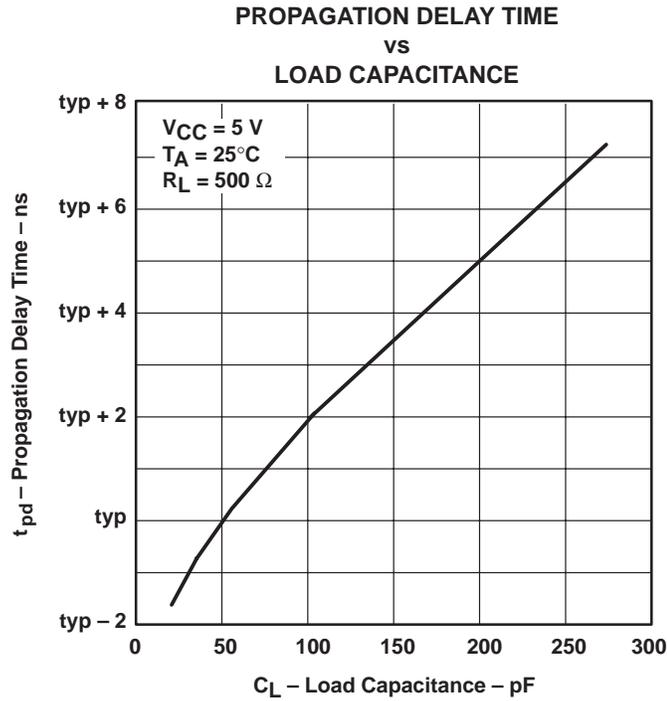


Figure 6

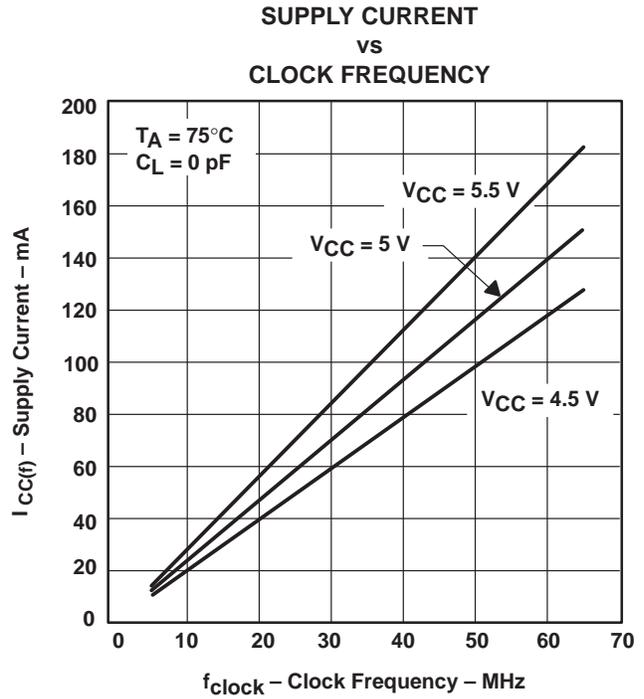


Figure 7

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
SN74ACT7813-15DL	Active	Production	SSOP (DL) 56	20 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	ACT7813-15
SN74ACT7813-15DL.A	Active	Production	SSOP (DL) 56	20 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	ACT7813-15

(1) **Status:** For more details on status, see our [product life cycle](#).

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

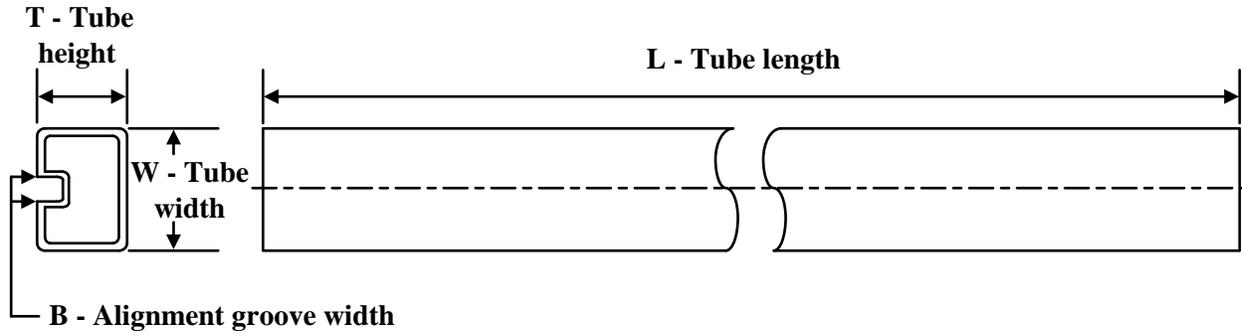
(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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TUBE


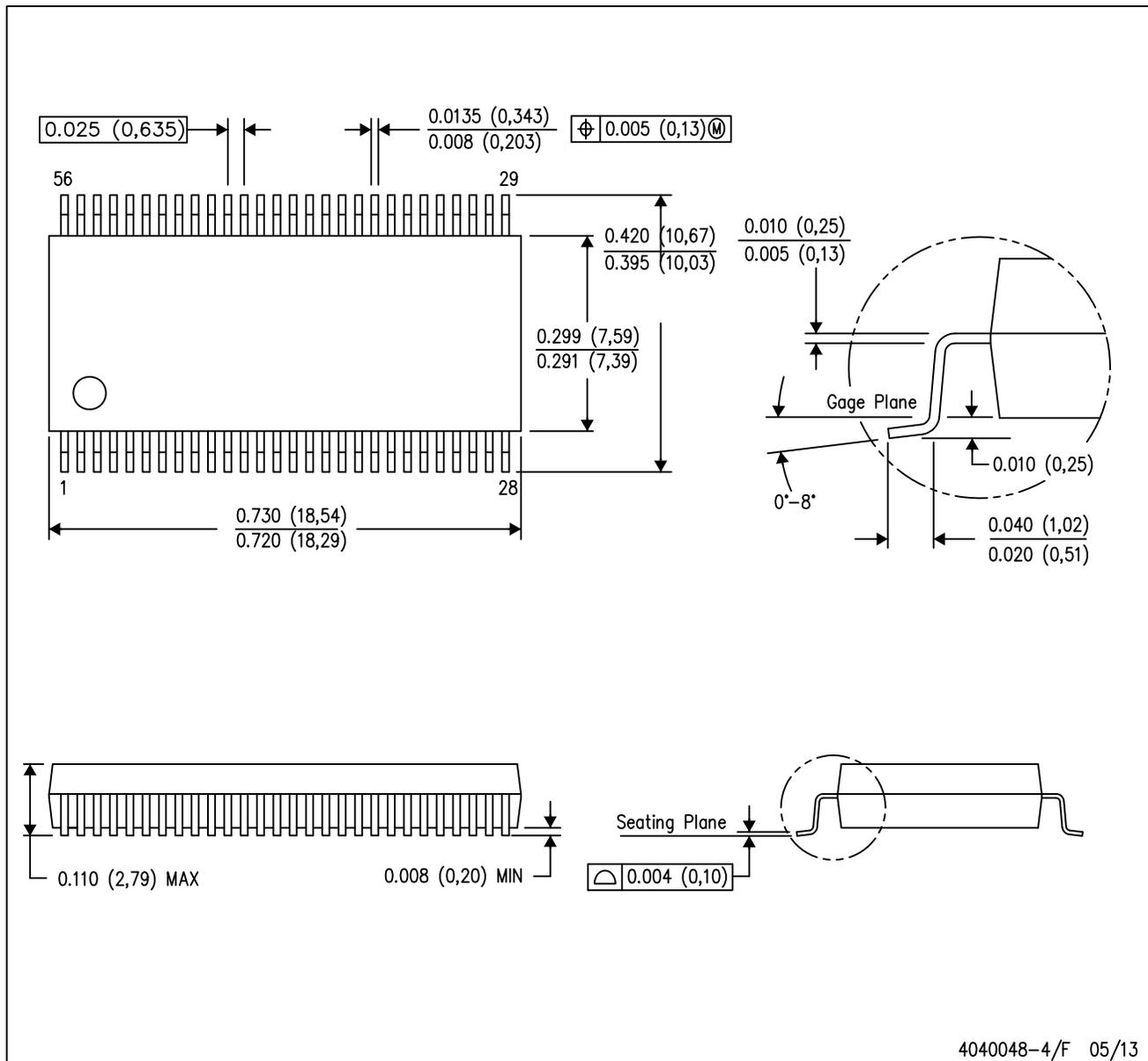
*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
SN74ACT7813-15DL	DL	SSOP	56	20	473.7	14.24	5110	7.87
SN74ACT7813-15DL.A	DL	SSOP	56	20	473.7	14.24	5110	7.87

MECHANICAL DATA

DL (R-PDSO-G56)

PLASTIC SMALL-OUTLINE PACKAGE



- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
 - D. Falls within JEDEC MO-118

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